

Supplementary Information

Controlling the threshold voltage of β -Ga₂O₃ field-effect transistors *via* remote fluorine plasma treatment

Janghyuk Kim[†], Marko J. Tadjer[‡], Michael A. Mastro[‡] and Jihyun Kim^{†,*}

[†]Department of Chemical and Biological Engineering, Korea University, Seoul 02841 Korea

[‡]US Naval Research Laboratory, 4555 Overlook Ave. SW, Washington, DC 20375 USA

Corresponding Author

*E-mail: hyunhyun7@korea.ac.kr (Jihyun Kim)

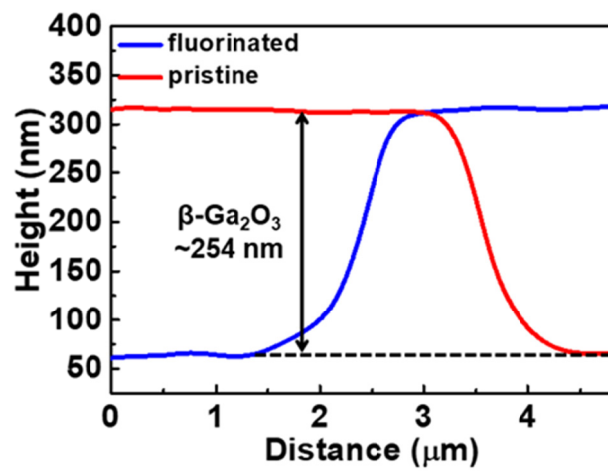


Figure S1 Height profile of pristine and fluorinated $\beta\text{-Ga}_2\text{O}_3$ flakes.

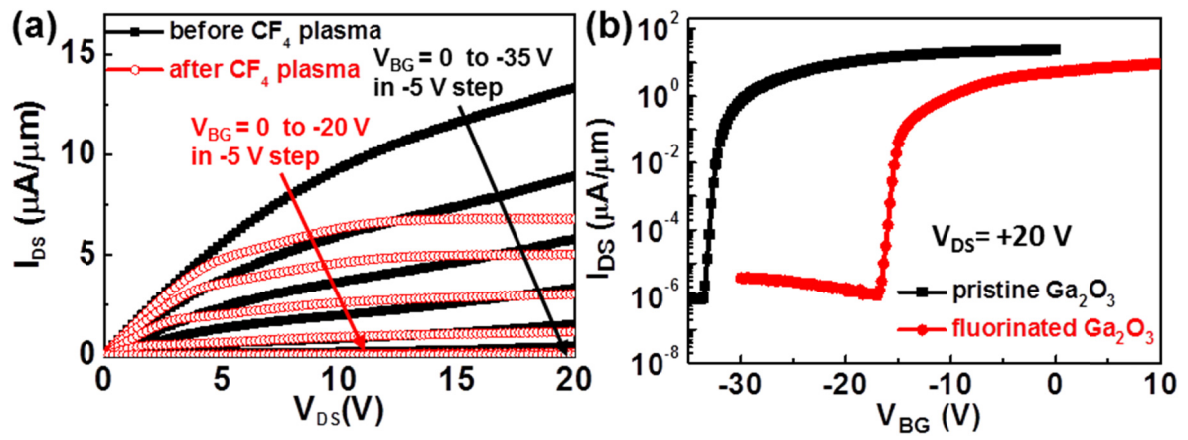


Figure S2 (a) $I_{\text{DS}}-V_{\text{DS}}$ output and (b) transfer characteristics of back-gated β - Ga_2O_3 MOSFETs before and after the CF_4 plasma treatment.

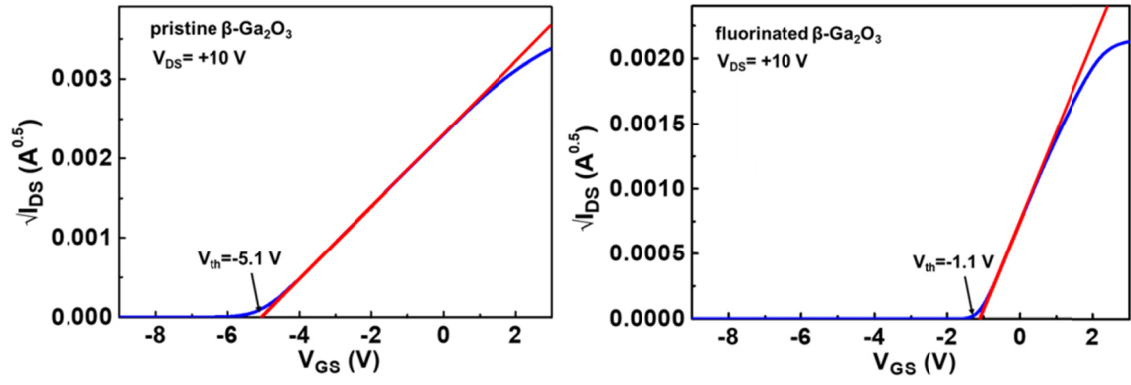


Figure S3 $I_D^{1/2}$ vs V_{GS} output characteristics of the pristine and fluorinated $\beta\text{-Ga}_2\text{O}_3$ MISFETs.